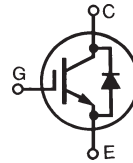


**XPT™ 650V IGBT  
GenX3™ w/ Diode**
**IXYH40N65B3D1  
IXYQ40N65B3D1**

 Extreme Light Punch Through  
IGBT for 5-30kHz Switching


$$V_{CES} = 650V$$

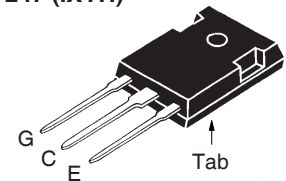
$$I_{C110} = 40A$$

$$V_{CE(sat)} \leq 2.0V$$

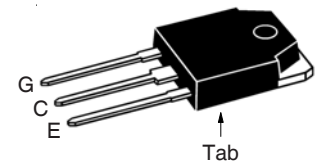
$$t_{fi(typ)} = 73ns$$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	650	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	650	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	86	A
$I_{C110}$	$T_C = 110^\circ C$	40	A
$I_{F110}$	$T_C = 110^\circ C$	50	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	195	A
$I_A$	$T_C = 25^\circ C$	20	A
$E_{AS}$	$T_C = 25^\circ C$	300	mJ
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 80$ @ $V_{CE} \leq V_{CES}$	A
$t_{sc}$ <b>(SCSOA)</b>	$V_{GE} = 15V$ , $V_{CE} = 360V$ , $T_J = 150^\circ C$ $R_G = 82\Omega$ , Non Repetitive	5	$\mu s$
$P_C$	$T_C = 25^\circ C$	300	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque	1.13/10	Nm/lb.in
<b>Weight</b>	TO-247	6.0	g
	TO-3P	5.5	g

TO-247 (IXYH)



TO-3P (IXYQ)



G = Gate                      C = Collector  
E = Emitter                  Tab = Collector

**Features**

- Optimized for Low 5-30kHz Switching
- Square RBSOA
- Anti-Parallel Fast Diode
- Avalanche Rated
- Short Circuit Capability

**Advantages**

- High Power Density
- Extremely Rugged
- Low Gate Drive Requirement

**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.5		6.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			10 $\mu A$ 1.5 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 40A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$		1.7 2.0	2.0 V V

Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 40\text{A}, V_{CE} = 10\text{V}$ , Note 1	16	27	S
$C_{ies}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1880	pF
$C_{oes}$			210	pF
$C_{res}$			43	pF
$Q_{g(on)}$	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		68	nC
$Q_{ge}$			10	nC
$Q_{gc}$			33	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 10\Omega$ Note 2		20	ns
$t_{ri}$			37	ns
$E_{on}$			0.80	mJ
$t_{d(off)}$			140	ns
$t_{fi}$			73	ns
$E_{off}$			0.70	1.25
$t_{d(on)}$	<b>Inductive load, <math>T_J = 150^\circ\text{C}</math></b> $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 10\Omega$ Note 2		20	ns
$t_{ri}$			37	ns
$E_{on}$			1.60	mJ
$t_{d(off)}$			176	ns
$t_{fi}$			174	ns
$E_{off}$			1.15	mJ
$R_{thJC}$			0.50	$^\circ\text{C/W}$
$R_{thCS}$		0.25		$^\circ\text{C/W}$

**Reverse Diode (FRED)**

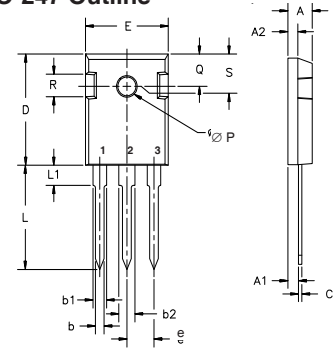
Symbol Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 30\text{A}, V_{GE} = 0\text{V}$ , Note 1			2.5
		$T_J = 150^\circ\text{C}$	1.2	V
$I_{rr}$	$I_F = 30\text{A}, V_{GE} = 0\text{V},$ $-di_F/dt = 500\text{A}/\mu\text{s}, V_R = 400\text{V}$	$T_J = 150^\circ\text{C}$	24	A
$t_{rr}$		$T_J = 150^\circ\text{C}$	125	ns
$R_{thJC}$				0.60 $^\circ\text{C/W}$

**Notes:**

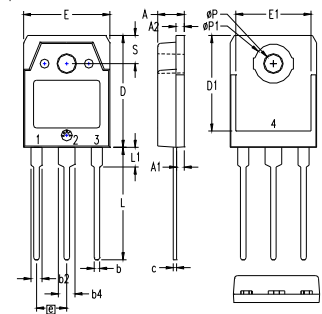
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{clamp})$ ,  $T_J$  or  $R_G$ .

**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

**TO-247 Outline**

 Terminals: 1 - Gate 2 - Collector  
 3 - Emitted

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

**TO-3P Outline**

 1 = Gate 2,4 = Collector  
 3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e		215 BSC		5.45 BSC
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
∅P	.126	.134	3.20	3.40
∅P1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

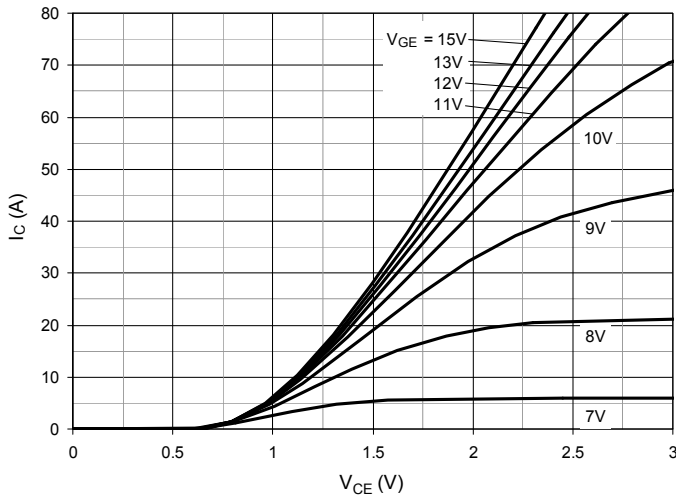


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

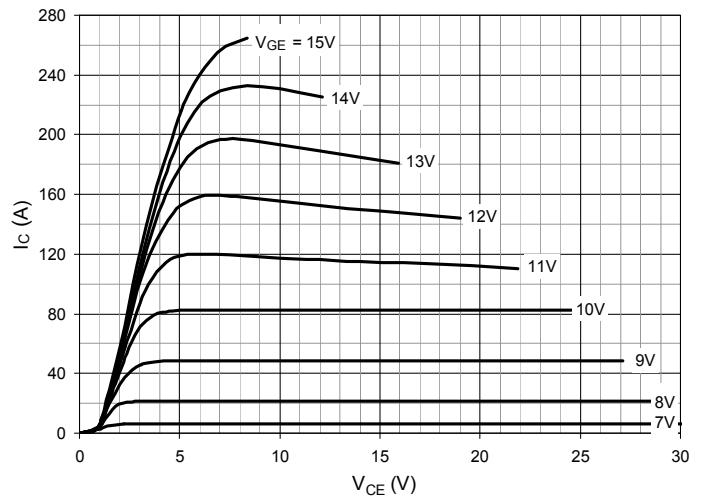


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

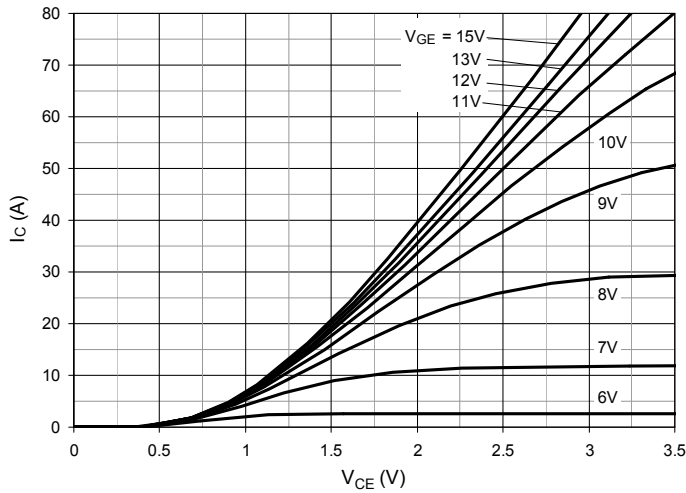


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

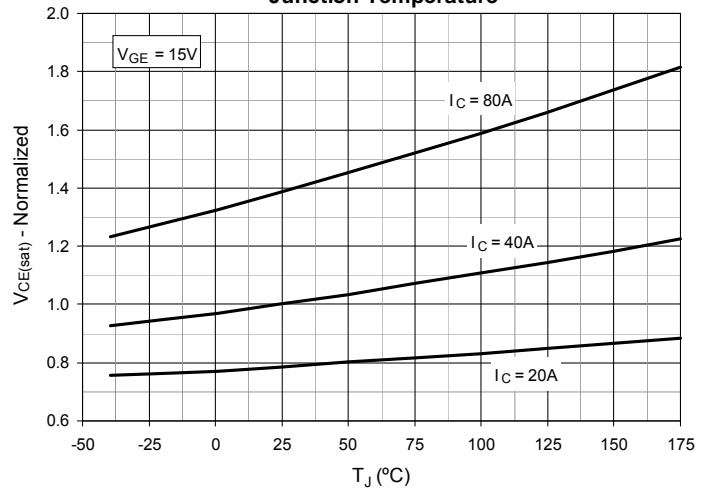


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

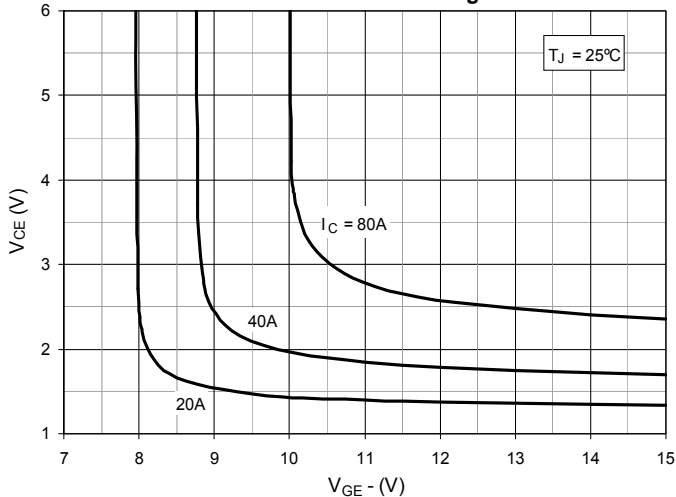


Fig. 6. Input Admittance

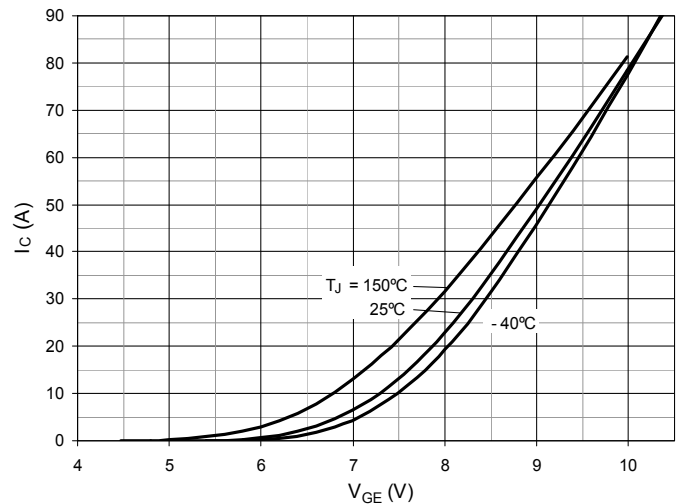


Fig. 7. Transconductance

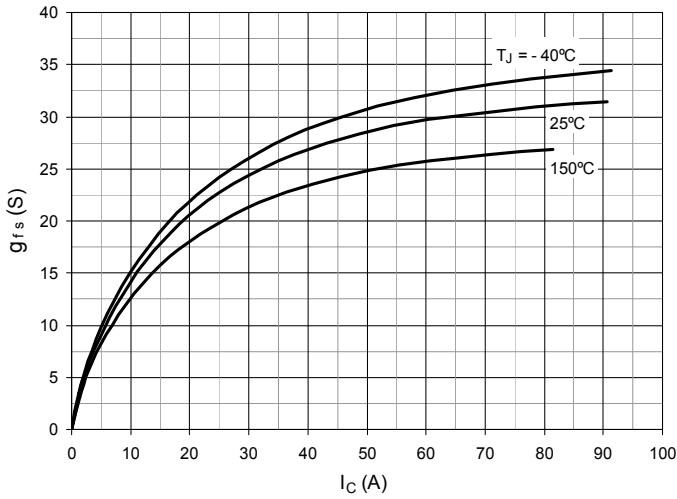


Fig. 8. Gate Charge

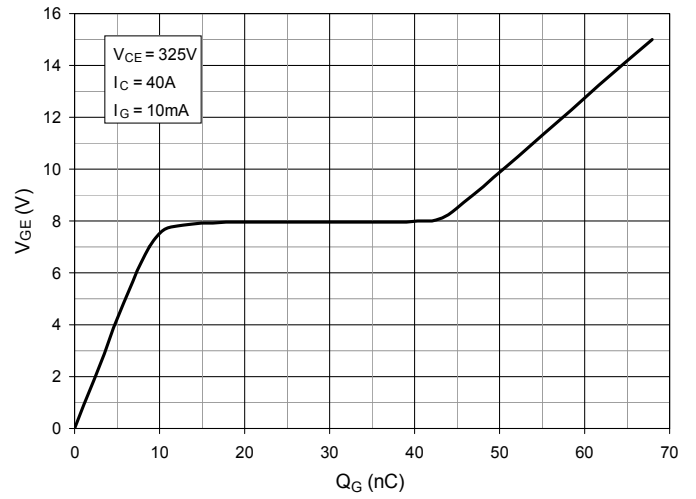


Fig. 9. Capacitance

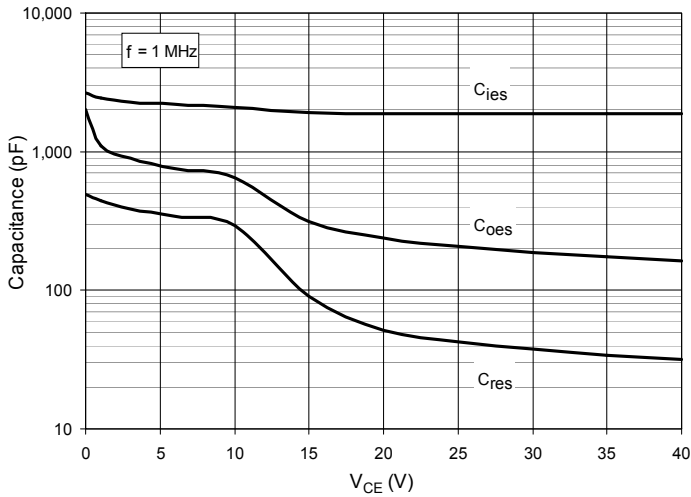


Fig. 10. Reverse-Bias Safe Operating Area

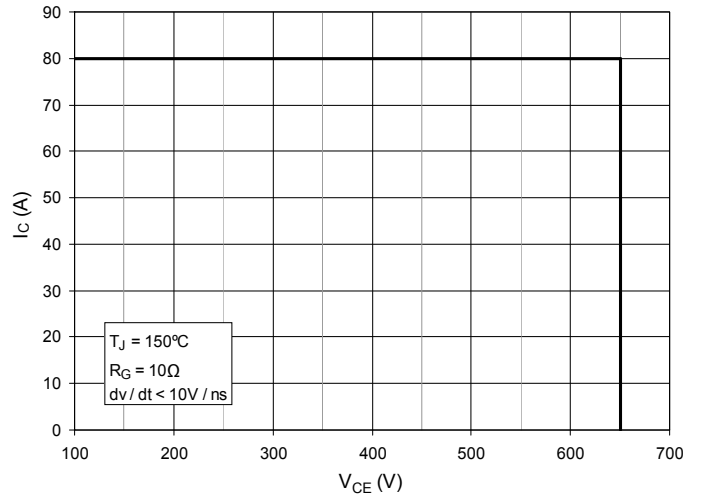


Fig. 11. Forward-Bias Safe Operating Area

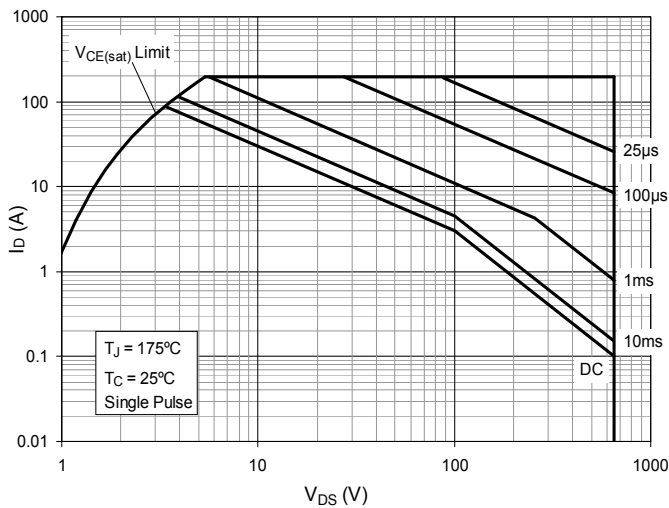
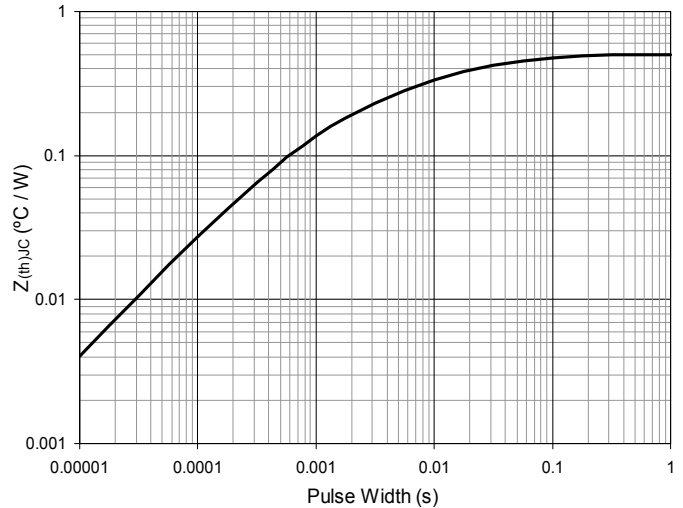
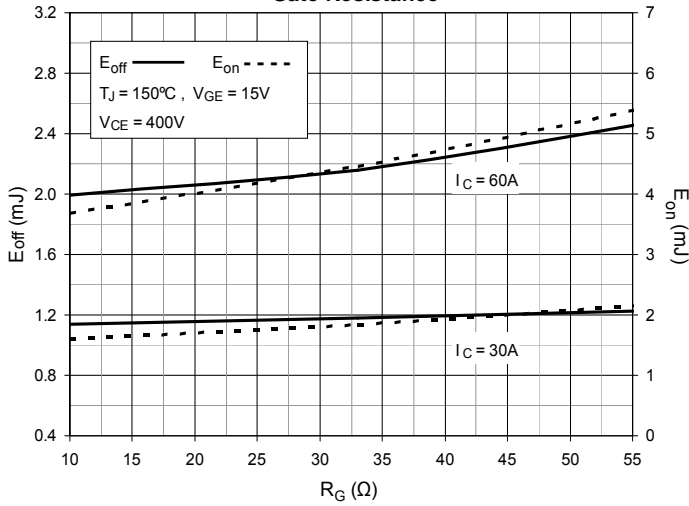


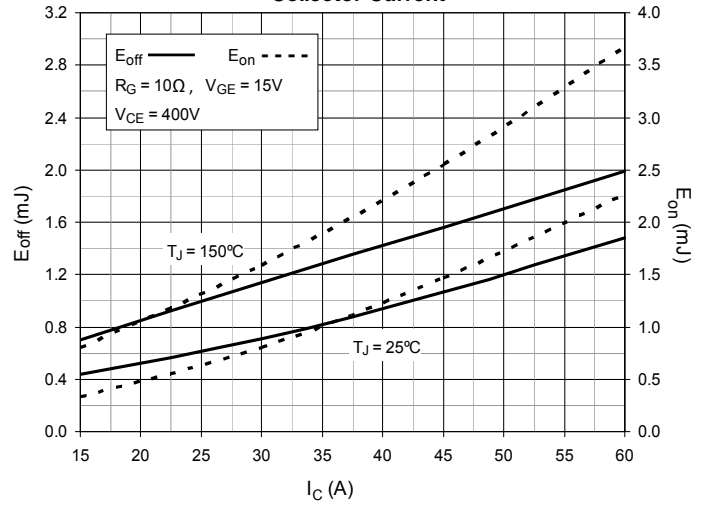
Fig. 12. Maximum Transient Thermal Impedance (IGBT)



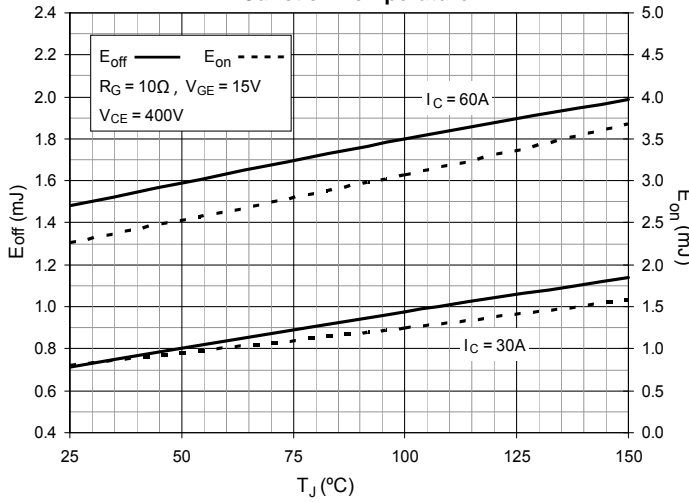
**Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance**



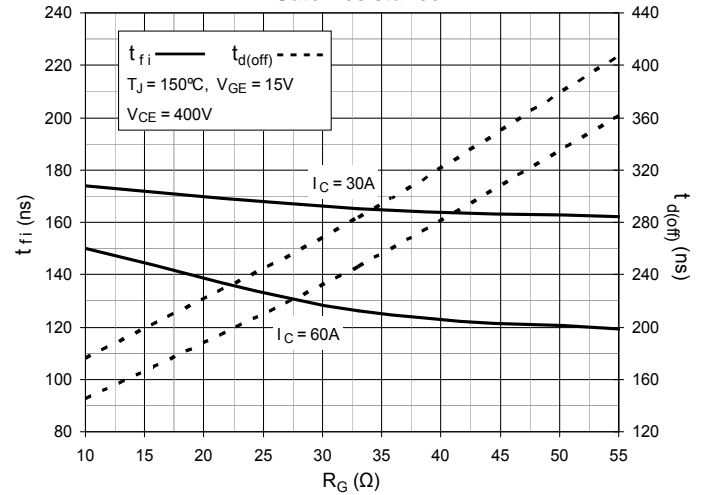
**Fig. 14. Inductive Switching Energy Loss vs. Collector Current**



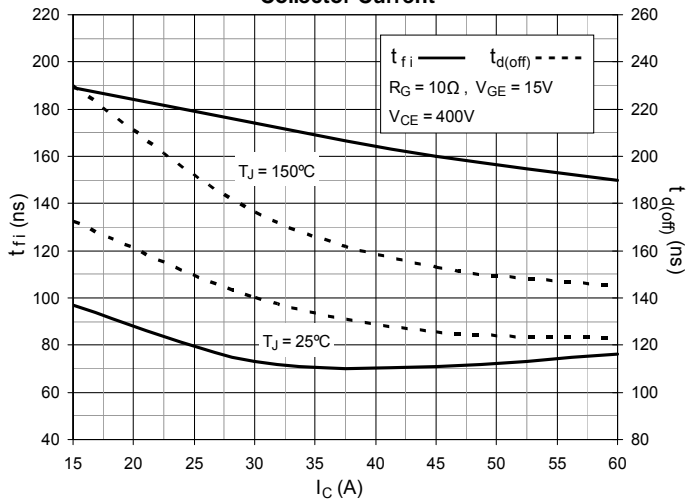
**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**



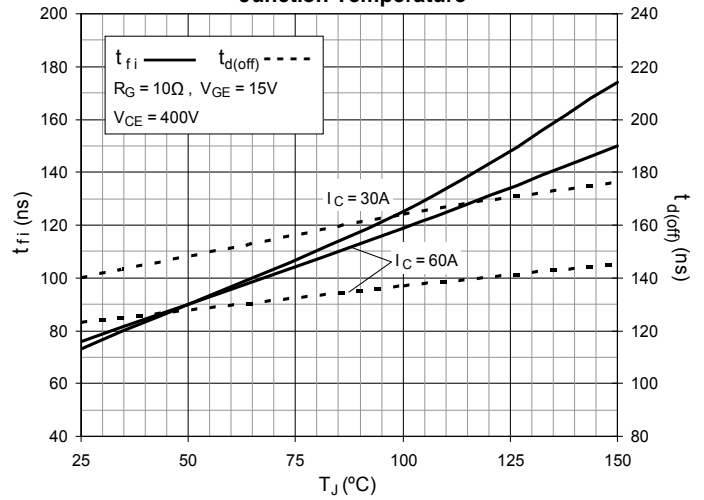
**Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance**



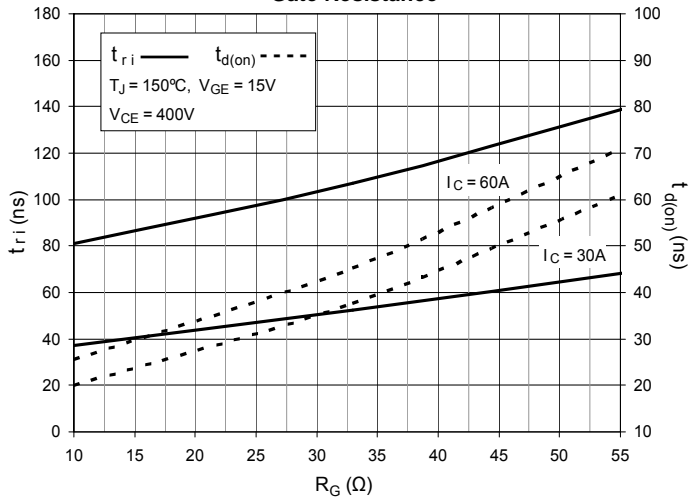
**Fig. 17. Inductive Turn-off Switching Times vs. Collector Current**



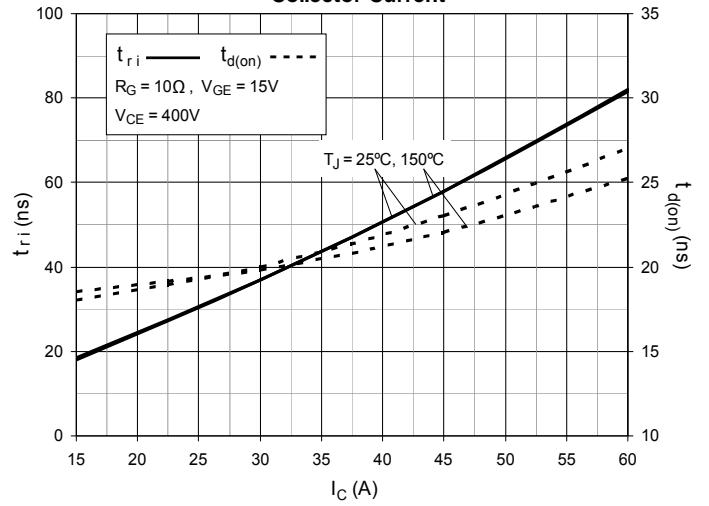
**Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 20. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature**

